TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2 S C 5 2 0 0

POWER AMPLIFIER APPLICATIONS

- Complementary to 2SA1943
- Recommended for 100W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	230	V
Collector-Emitter Voltage	v_{CEO}	230	V
Emitter-Base Voltage	v_{EBO}	5	v
Collector Current	$I_{\mathbf{C}}$	15	A
Base Current	$I_{\mathbf{B}}$	1.5	Α
Collector Power Dissipation (Tc=25°C)	PC	150	w
Junction Temperature	$T_{\mathbf{j}}$	150	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	$^{\circ}\mathrm{C}$

Unit in mm 20.5MAX \$3.3 ± 0.2 20.0±0.6 0.6-0.7 COLLECTOR (HEAT SINK) 2. **EMITTER** JEDEC EIAJ TOSHIBA 2-21F1A

Weight: 9.75g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	$V_{CB} = 230V, I_{E} = 0$	_		5.0	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	_	_	5.0	μ A
Collector-Emitter Breakdown Voltage	V _(BR) CEO	$I_{\rm C} = 50 { m mA}, I_{\rm B} = 0$	230	_	_	v
DC Current Gain	hFE (1) (Note)	$V_{\text{CE}} = 5V$, $I_{\text{C}} = 1A$	55	_	160	
	h _{FE (2)}	$V_{CE}=5V$, $I_{C}=7A$	35	60		
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_{C}=8A, I_{B}=0.8A$	_	0.40	3.0	V
Base-Emitter Voltage	$ m v_{BE}$	$V_{CE}=5V$, $I_{C}=7A$		1.0	1.5	V
Transition Frequency	$\mathbf{f_{T}}$	$V_{CE}=5V$, $I_{C}=1A$	_	30	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	200	_	рF

Note: hFE(1) Classification $R: 55\sim110, O: 80\sim160$

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